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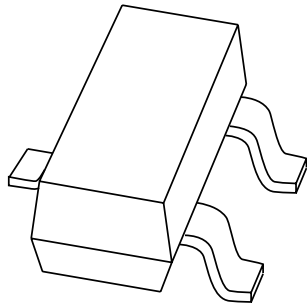
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Kind regards,

Team Nexperia

# DATA SHEET



**PBSS9110T**

100 V, 1 A

PNP low  $V_{CEsat}$  (BISS) transistor

Product data sheet  
Supersedes data of 2004 May 06

2004 May 13

# 100 V, 1 A PNP low $V_{CEsat}$ (BISS) transistor

**PBSS9110T**

**FEATURES**

- SOT23 package
- Low collector-emitter saturation voltage  $V_{CEsat}$
- High collector current capability:  $I_C$  and  $I_{CM}$
- Higher efficiency leading to less heat generation

**APPLICATIONS**

- Major application segments
  - Automotive 42 V power
  - Telecom infrastructure
  - Industrial
- DC-to-DC conversion
- Peripheral drivers
  - Driver in low supply voltage applications (e.g. lamps and LEDs).
  - Inductive load driver (e.g. relays, buzzers and motors).

**DESCRIPTION**

PNP low  $V_{CEsat}$  transistor in a SOT23 plastic package.  
NPN complement: PBSS8110T.

**MARKING**

| TYPE NUMBER | MARKING CODE <sup>(1)</sup> |
|-------------|-----------------------------|
| PBSS9110T   | *U7                         |

**Note**

- \* = p: Made in Hong Kong.  
\* = t: Made in Malaysia.  
\* = W: Made in China.

**ORDERING INFORMATION**

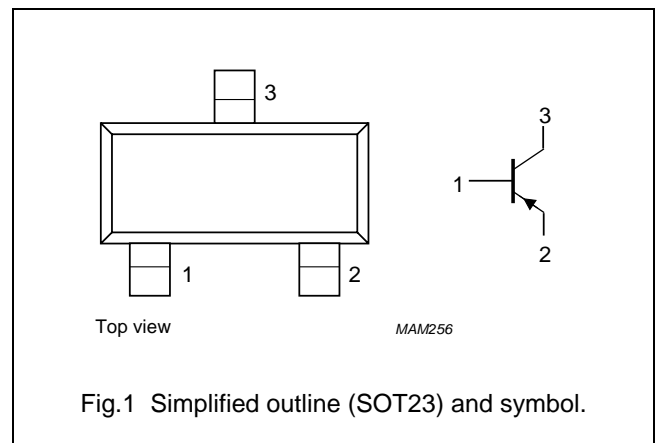
| TYPE NUMBER | PACKAGE |  |         |
|-------------|---------|--|---------|
|             | NAME    | DESCRIPTION                              | VERSION |
| PBSS9110T   | –       | plastic surface mounted package; 3 leads | SOT23   |

**QUICK REFERENCE DATA**

| SYMBOL      | PARAMETER                         | MAX. | UNIT       |
|-------------|-----------------------------------|------|------------|
| $V_{CEO}$   | collector-emitter voltage         | –100 | V          |
| $I_C$       | collector current (DC)            | –1   | A          |
| $I_{CM}$    | repetitive peak collector current | –3   | A          |
| $R_{CEsat}$ | equivalent on-resistance          | 320  | m $\Omega$ |

**PINNING**

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | base        |
| 2   | emitter     |
| 3   | collector   |



100 V, 1 A  
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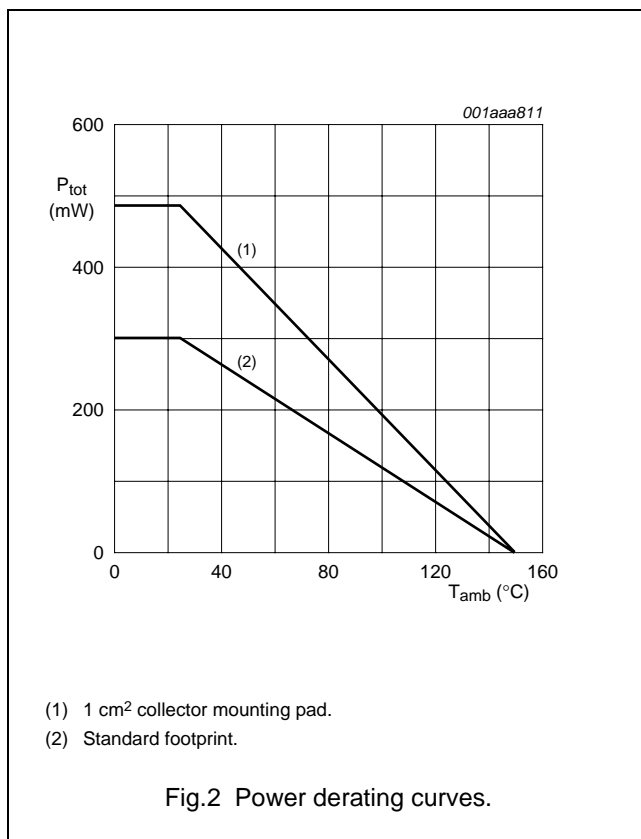
**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL    | PARAMETER                     | CONDITIONS                           | MIN. | MAX. | UNIT |
|-----------|-------------------------------|--------------------------------------|------|------|------|
| $V_{CBO}$ | collector-base voltage        | open emitter                         | –    | –120 | V    |
| $V_{CEO}$ | collector-emitter voltage     | open base                            | –    | –100 | V    |
| $V_{EBO}$ | emitter-base voltage          | open collector                       | –    | –5   | V    |
| $I_C$     | collector current (DC)        |                                      | –    | –1   | A    |
| $I_{CM}$  | peak collector current        | limited by $T_{j(max)}$              | –    | –3   | A    |
| $I_B$     | base current (DC)             |                                      | –    | –300 | mA   |
| $P_{tot}$ | total power dissipation       | $T_{amb} \leq 25\text{ °C}$ ; note 1 | –    | 300  | mW   |
|           |                               | $T_{amb} \leq 25\text{ °C}$ ; note 2 | –    | 480  | mW   |
| $T_j$     | junction temperature          |                                      | –    | 150  | °C   |
| $T_{amb}$ | operating ambient temperature |                                      | –65  | +150 | °C   |
| $T_{stg}$ | storage temperature           |                                      | –65  | +150 | °C   |

**Notes**

1. Device mounted on a printed-circuit board, single-sided copper, tin-plated, standard footprint.
2. Device mounted on a printed-circuit board, single-sided copper, tin-plated and 1 cm<sup>2</sup> collector mounting pad.



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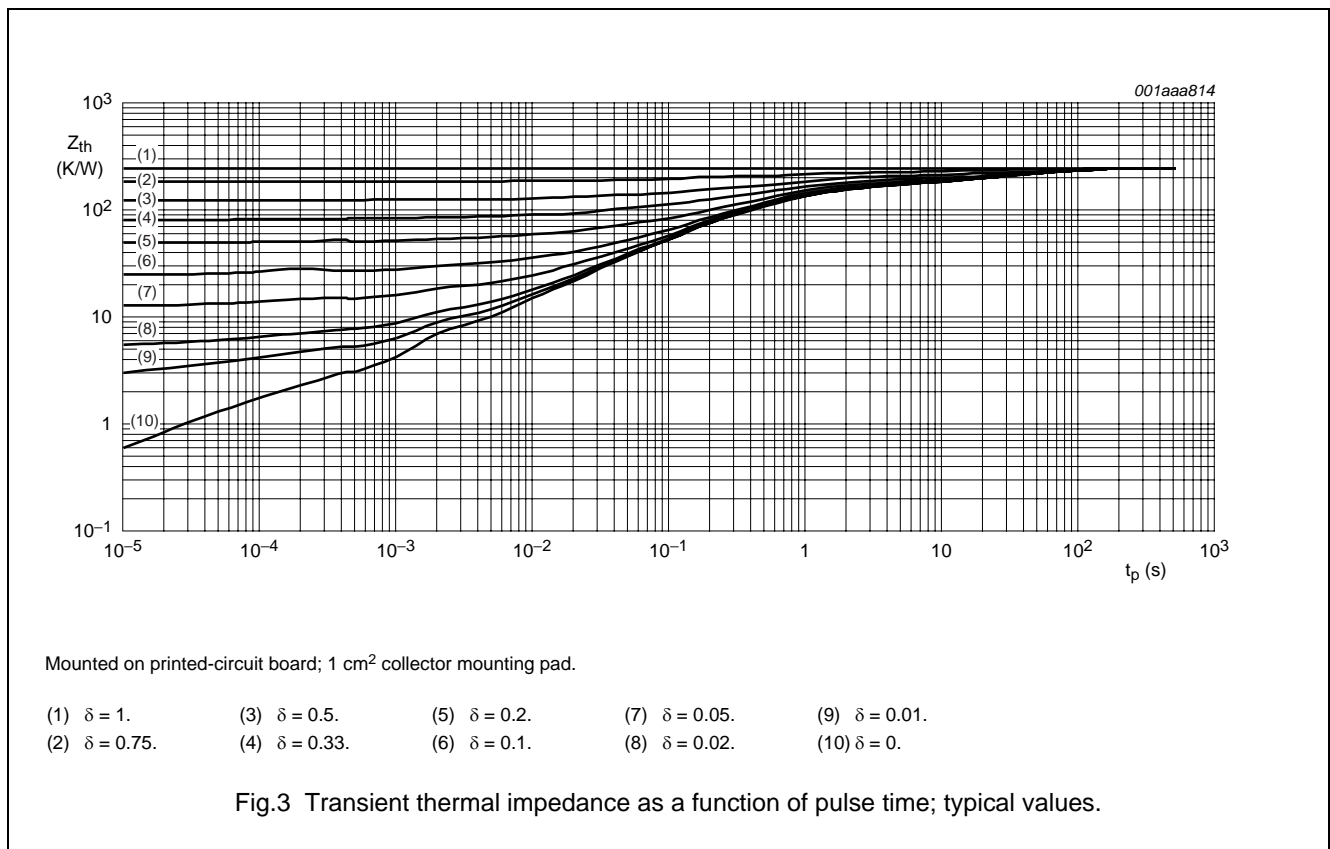
PBSS9110T

**THERMAL CHARACTERISTICS**

| SYMBOL        | PARAMETER                                   | CONDITIONS          | VALUE | UNIT |
|---------------|---|---------------------|-------|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air; note 1 | 417   | K/W  |
|               |   | in free air; note 2 | 260   | K/W  |

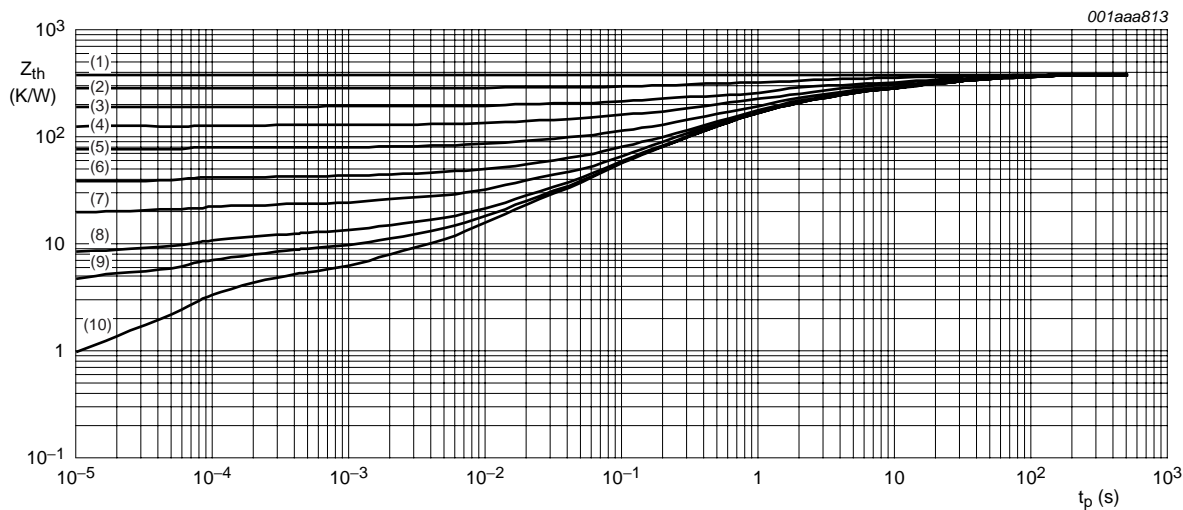
**Notes**

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2. Device mounted on a printed-circuit board, single-sided copper, tin-plated and 1 cm<sup>2</sup> collector mounting pad.



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Mounted on printed-circuit board; standard footprint.

- |                      |                      |                     |                      |                      |
|----------------------|----------------------|---------------------|----------------------|----------------------|
| (1) $\delta = 1.$    | (3) $\delta = 0.5.$  | (5) $\delta = 0.2.$ | (7) $\delta = 0.05.$ | (9) $\delta = 0.01.$ |
| (2) $\delta = 0.75.$ | (4) $\delta = 0.33.$ | (6) $\delta = 0.1.$ | (8) $\delta = 0.02.$ | (10) $\delta = 0.$   |

Fig.4 Transient thermal impedance as a function of pulse time; typical values.

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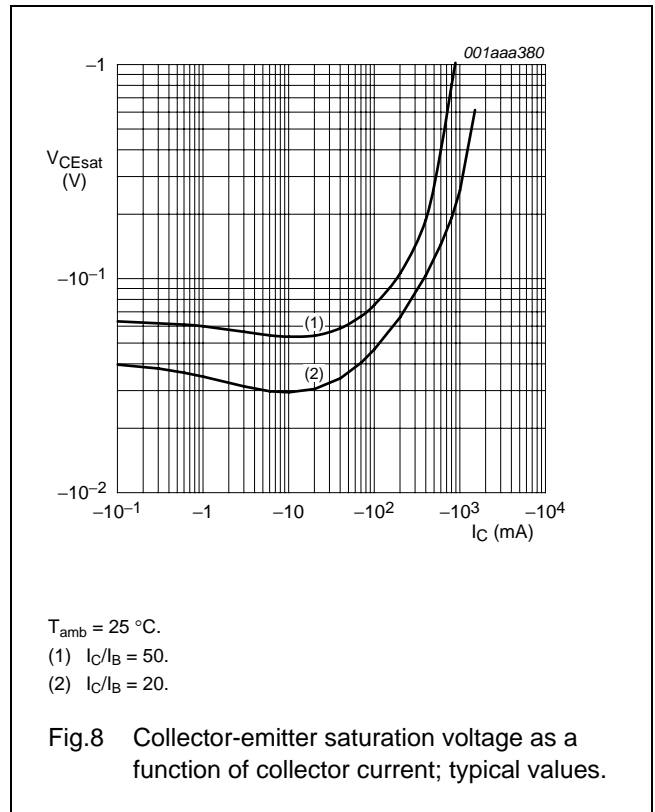
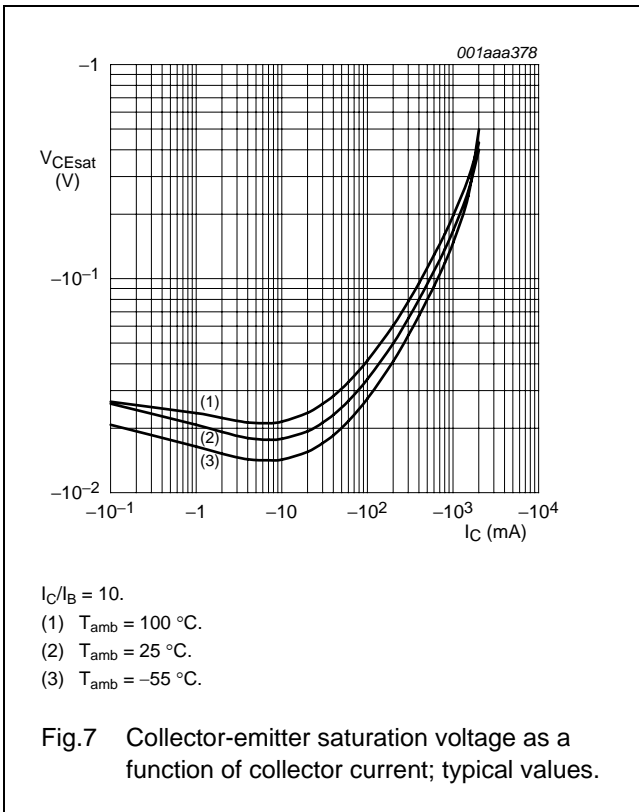
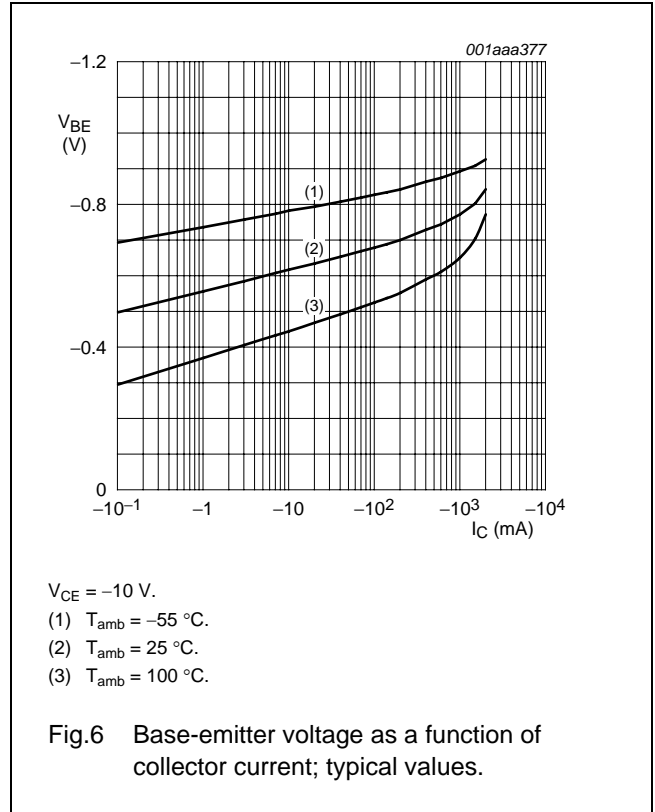
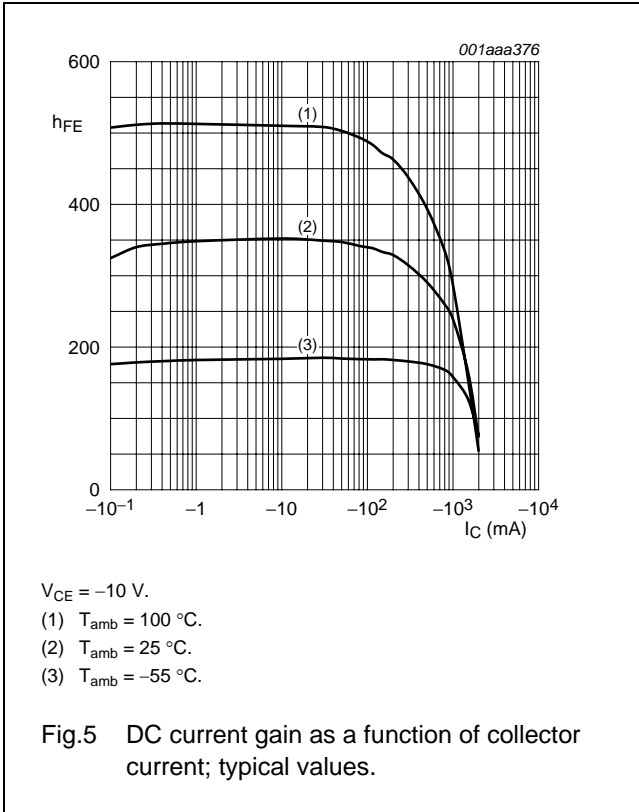
**CHARACTERISTICS** $T_j = 25\text{ °C}$  unless otherwise specified.

| SYMBOL      | PARAMETER                            | CONDITIONS  | MIN. | TYP. | MAX. | UNIT             |
|-------------|--------------------------------------|---|------|------|------|------------------|
| $I_{CBO}$   | collector-base cut-off current       | $V_{CB} = -80\text{ V}; I_E = 0\text{ A}$                               | –    | –    | –100 | nA               |
|             |                                      | $V_{CB} = -80\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ °C}$          | –    | –    | –50  | $\mu\text{A}$    |
| $I_{CES}$   | collector-emitter cut-off current    | $V_{CE} = -80\text{ V}; V_{BE} = 0\text{ A}$                            | –    | –    | –100 | nA               |
| $I_{EBO}$   | emitter-base cut-off current         | $V_{EB} = -4\text{ V}; I_C = 0\text{ A}$                                | –    | –    | –100 | nA               |
| $h_{FE}$    | DC current gain                      | $V_{CE} = -5\text{ V}; I_C = -1\text{ mA}$                              | 150  | –    | –    |                  |
|             |                                      | $V_{CE} = -5\text{ V}; I_C = -250\text{ mA}$                            | 150  | –    | –    |                  |
|             |                                      | $V_{CE} = -5\text{ V}; I_C = -500\text{ mA}$ ; note 1                   | 150  | –    | 450  |                  |
|             |                                      | $V_{CE} = -5\text{ V}; I_C = -1\text{ A}$ ; note 1                      | 125  | –    | –    |                  |
| $V_{CEsat}$ | collector-emitter saturation voltage | $I_C = -250\text{ mA}; I_B = -25\text{ mA}$                             | –    | –    | –120 | mV               |
|             |                                      | $I_C = -500\text{ mA}; I_B = -50\text{ mA}$                             | –    | –    | –180 | mV               |
|             |                                      | $I_C = -1\text{ A}; I_B = -100\text{ mA}$ ; note 1                      | –    | –    | –320 | mV               |
| $R_{CEsat}$ | equivalent on-resistance             | $I_C = -1\text{ A}; I_B = -100\text{ mA}$ ; note 1                      | –    | 170  | 320  | $\text{m}\Omega$ |
| $V_{BEsat}$ | base-emitter saturation voltage      | $I_C = -1\text{ A}; I_B = -100\text{ mA}$                               | –    | –    | –1.1 | V                |
| $V_{BEon}$  | base-emitter turn-on voltage         | $V_{CE} = -5\text{ V}; I_C = -1\text{ A}$                               | –    | –    | –1   | V                |
| $f_T$       | transition frequency                 | $V_{CE} = -10\text{ V}; I_C = -50\text{ mA}$ ;<br>$f = 100\text{ MHz}$  | 100  | –    | –    | MHz              |
| $C_c$       | collector capacitance                | $V_{CB} = -10\text{ V}; I_E = I_e = 0\text{ A}$ ;<br>$f = 1\text{ MHz}$ | –    | –    | 17   | pF               |

**Note**1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

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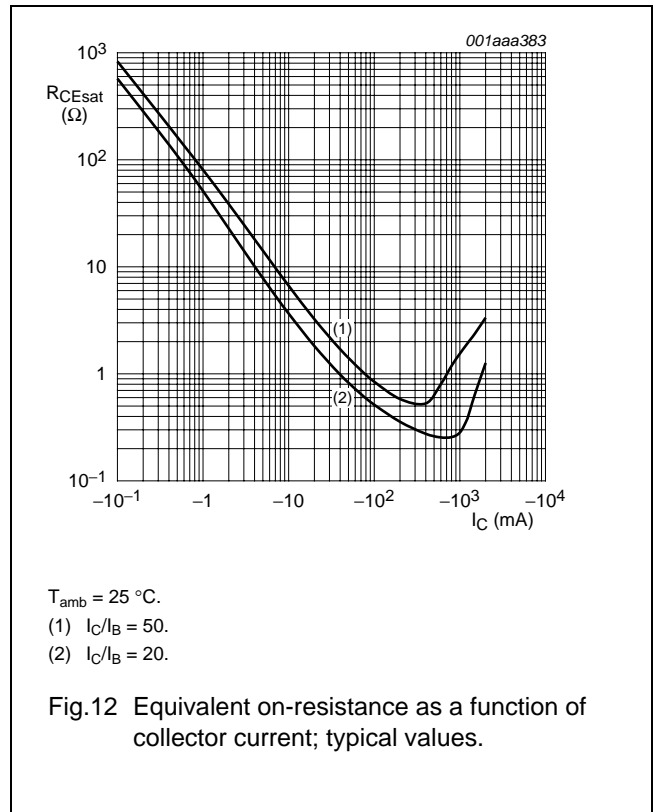
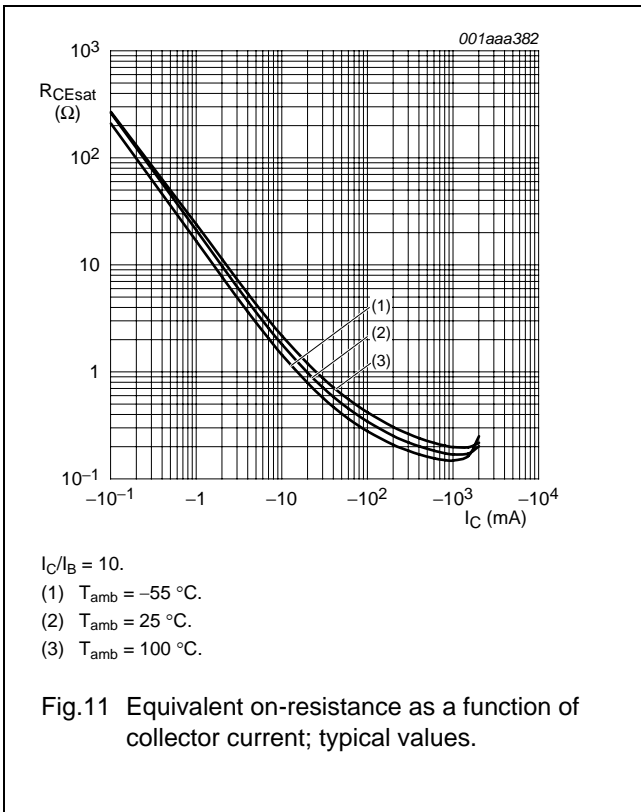
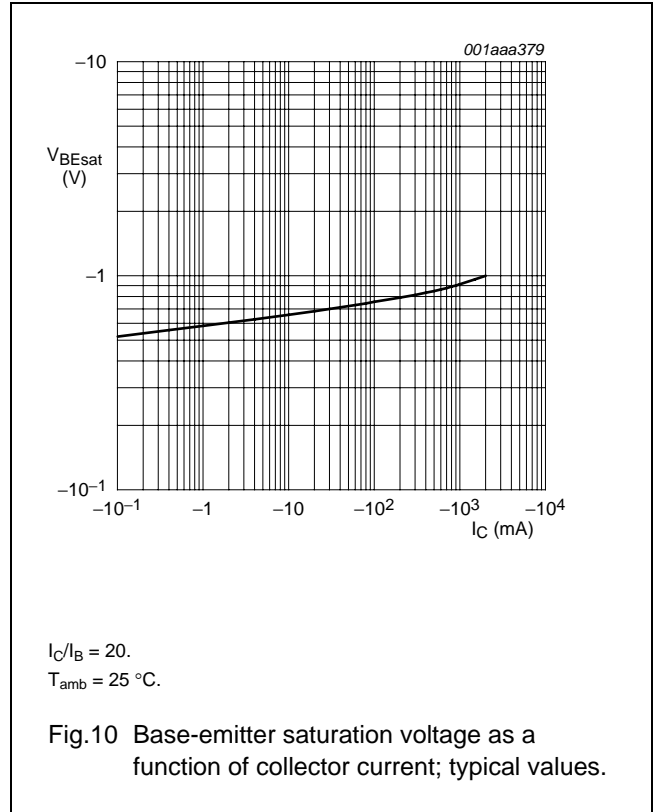
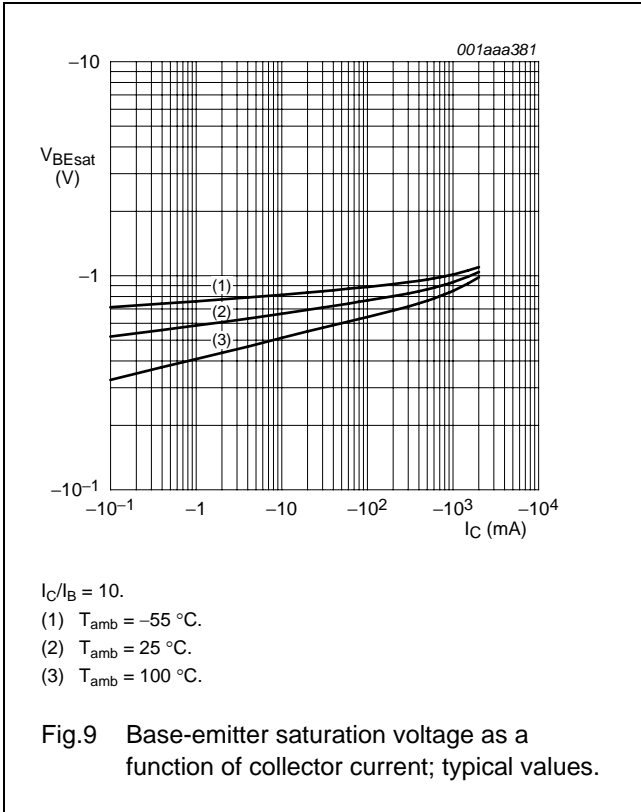
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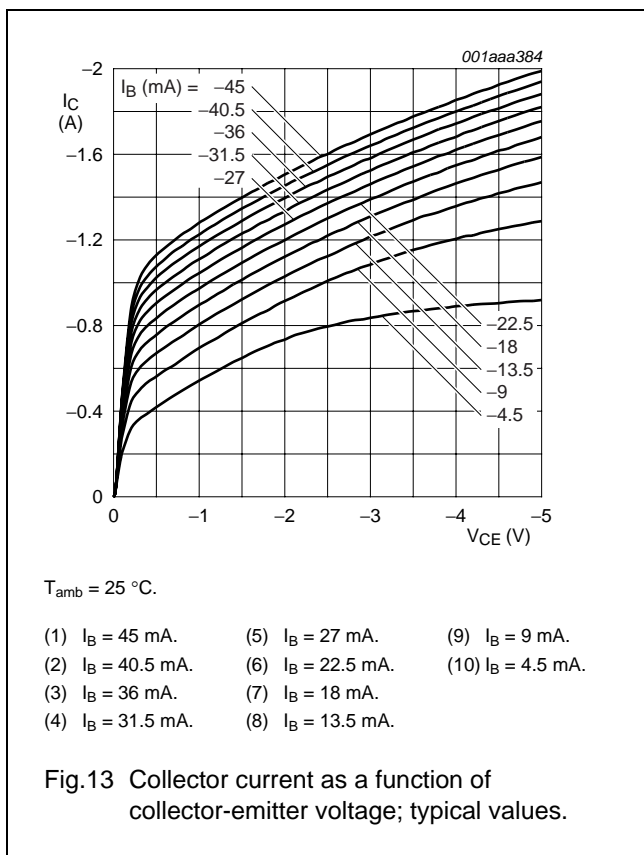
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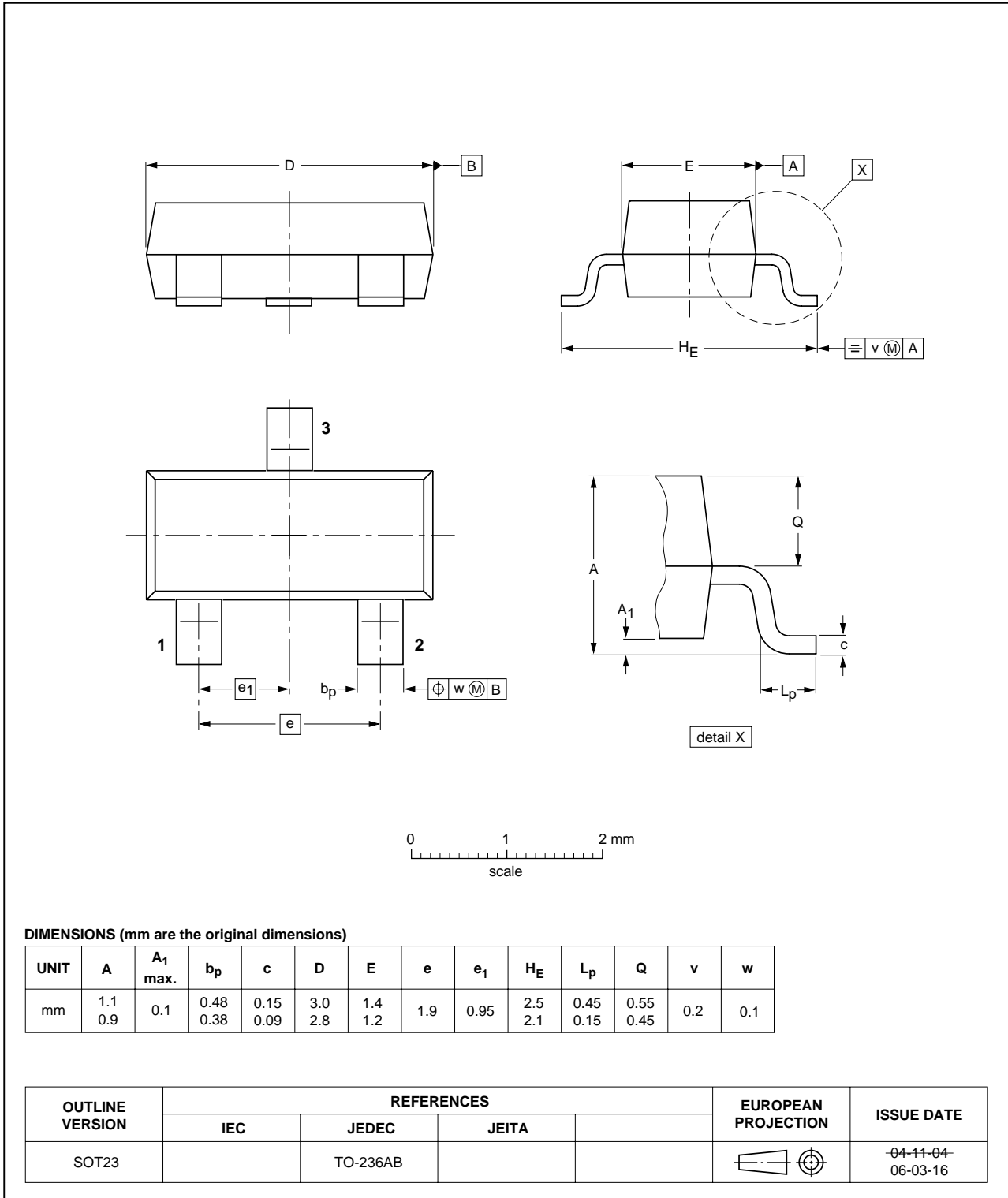
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PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



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PBSS9110T

**DATA SHEET STATUS**

| DOCUMENT STATUS <sup>(1)</sup> | PRODUCT STATUS <sup>(2)</sup> | DEFINITION  |
|--------------------------------|-------------------------------|---|
| Objective data sheet           | Development                   | This document contains data from the objective specification for product development. |
| Preliminary data sheet         | Qualification                 | This document contains data from the preliminary specification.                       |
| Product data sheet             | Production                    | This document contains the product specification.                                     |

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## **Contact information**

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